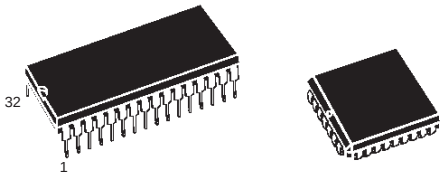
M27C405

4 Mbit (512Kb x 8) OTP EPROM

- 5V ± 10% SUPPLY VOLTAGE in READ OPERATION
- PIN COMPATIBLE with the 4 Mbit, SINGLE VOLTAGE FLASH MEMORY
- FAST ACCESS TIME: 70ns
- LOW POWER CONSUMPTION:
  - Active Current 30mA at 5MHz
  - Standby Current 100µA
- PROGRAMMING VOLTAGE: 12.75V ± 0.25V
- PROGRAMMING TIMES
  - Typical 48sec. (PRESTO II Algorithm)
  - Typical 27sec. (On-Board Programming)
- ELECTRONIC SIGNATURE
  - Manufacturer Code: 20h
  - Device Code: B4



PDIP32 (B)

PLCC32 (K)

TSOP32 (N)
8 x 20mm

DESCRIPTION

The M27C405 is a 4 Mbit EPROM offered in the OTP (one time programmable) range. It is ideally suited for microprocessor systems requiring large programs, in the application where the contents is stable and needs to be programmed only one time and is organised as 524,288 by 8 bits.

The M27C405 is pin compatible with the industry standard 4 Mbit, single voltage Flash memory. It can be considered as a Flash Low Cost solution for production quantities.

The M27C405 is offered in PDIP32, PLCC32 and TSOP32 (8 x 20 mm) packages.

Table 1. Signal Names

A0-A18	Address Inputs
Q0-Q7	Data Outputs
$\overline{E}$	Chip Enable
$\overline{G}$	Output Enable
V_{PP}	Program Supply
V_{CC}	Supply Voltage
V_{SS}	Ground

Figure 1. Logic Diagram

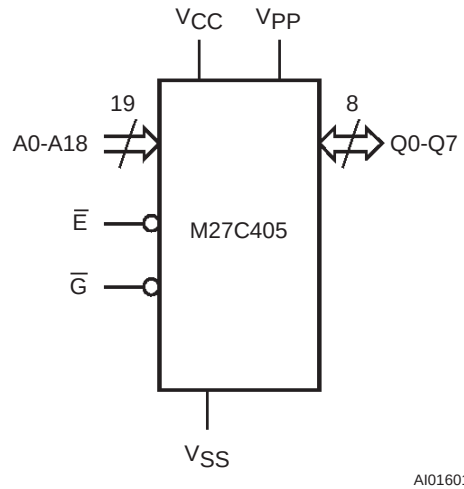


Figure 2A. DIP Pin Connections

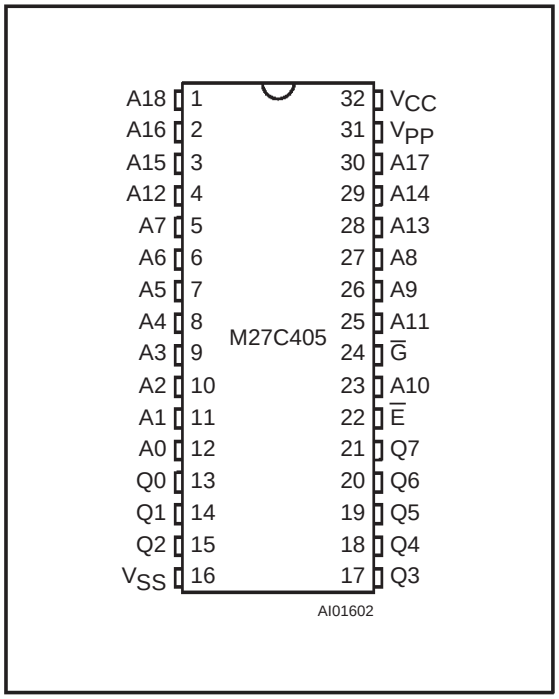


Figure 2B. LCC Pin Connections

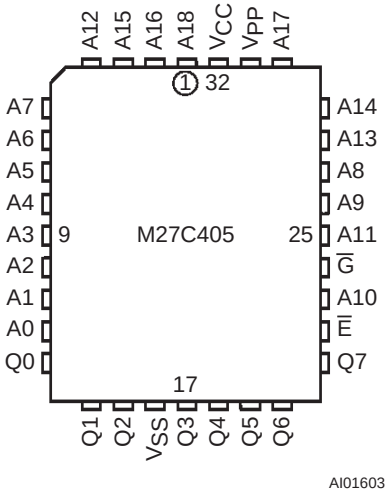
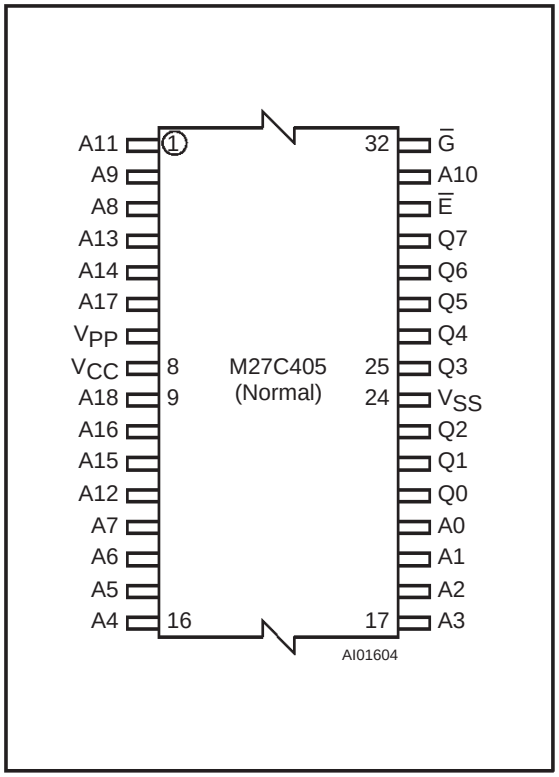


Figure 2C. TSOP Pin Connections



DEVICE OPERATION

The modes of operations of the M27C405 are listed in the Operating Modes table. A single power supply is required in the read mode. All inputs are TTL levels except for V_{pp} and 12V on A9 for Electronic Signature.

Read Mode

The M27C405 has two control functions, both of which must be logically active in order to obtain data at the outputs. Chip Enable ($\overline{E}$) is the power control and should be used for device selection. Output Enable ($\overline{G}$) is the output control and should be used to gate data to the output pins, independent of device selection. Assuming that the addresses are stable, the address access time (t_{AVQV}) is equal to the delay from $\overline{E}$ to output (t_{ELQV}). Data is available at the output after a delay of t_{GLQV} from the falling edge of $\overline{G}$, assuming that $\overline{E}$ has been low and the addresses have been stable for at least t_{AVQV}-t_{GLQV}.

Standby Mode

The M27C405 has a standby mode which reduces the active current from 30mA to 100µA. The M27C405 is placed in the standby mode by applying a CMOS high signal to the $\overline{E}$ input. When in the standby mode, the outputs are in a high impedance state, independent of the $\overline{G}$ input.

Table 2. Absolute Maximum Ratings (1)

Symbol	Parameter	Value	Unit
T_A	Ambient Operating Temperature (3)	–40 to 125	°C
T_{BIAS}	Temperature Under Bias	–50 to 125	°C
T_{STG}	Storage Temperature	–65 to 150	°C
V_{IO} (2)	Input or Output Voltages (except A9)	–2 to 7	V
V_{CC}	Supply Voltage	–2 to 7	V
V_{A9} (2)	A9 Voltage	–2 to 13.5	V
V_{PP}	Program Supply Voltage	–2 to 14	V

Notes: 1. Except for the rating "Operating Temperature Range", stresses above those listed in the Table "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.
2. Minimum DC voltage on Input or Output is –0.5V with possible undershoot to –2.0V for a period less than 20ns. Maximum DC voltage on Output is V_{CC} +0.5V with possible overshoot to V_{CC} +2V for a period less than 20ns.
3. Depends on range.

Table 3. Operating Modes

Mode	$\overline{E}$	$\overline{G}$	A9	V_{PP}	Q0 - Q7
Read	V_{IL}	V_{IL}	X	V_{CC} or V_{SS}	Data Out
Output Disable	V_{IL}	V_{IH}	X	V_{CC} or V_{SS}	Hi-Z
Program	V_{IL} Pulse	V_{IH}	X	V_{PP}	Data In
Verify	V_{IH}	V_{IL}	X	V_{PP}	Data Out
Program Inhibit	V_{IH}	V_{IH}	X	V_{PP}	Hi-Z
Standby	V_{IH}	X	X	V_{CC} or V_{SS}	Hi-Z
Electronic Signature	V_{IL}	V_{IL}	V_{ID}	V_{CC}	Codes

Note: X = V_{IH} or V_{IL}, V_{ID} = 12V ± 0.5V

Table 4. Electronic Signature

Identifier	A0	Q7	Q6	Q5	Q4	Q3	Q2	Q1	Q0	Hex Data
Manufacturer's Code	V_{IL}	0	0	1	0	0	0	0	0	20h
Device Code	V_{IH}	1	0	1	1	0	1	0	0	B4h

Two Line Output Control

Because OTP EPROMs are usually used in larger memory arrays, this product features a 2 line control function which accommodates the use of multiple memory connection. The two line control function allows:

a. the lowest possible memory power dissipation,
b. complete assurance that output bus contention will not occur.

For the most efficient use of these two control lines, $\overline{E}$ should be decoded and used as the primary device selecting function, while $\overline{G}$ should be made a common connection to all devices in the array and connected to the $\overline{READ}$ line from the system control bus. This ensures that all deselected memory devices are in their low power standby mode and that the output pins are only active when data is required from a particular memory device.

Table 5. AC Measurement Conditions

	High Speed	Standard
Input Rise and Fall Times	≤ 10ns	≤ 20ns
Input Pulse Voltages	0 to 3V	0.4V to 2.4V
Input and Output Timing Ref. Voltages	1.5V	0.8V and 2V

Figure 3. AC Testing Input Output Waveform

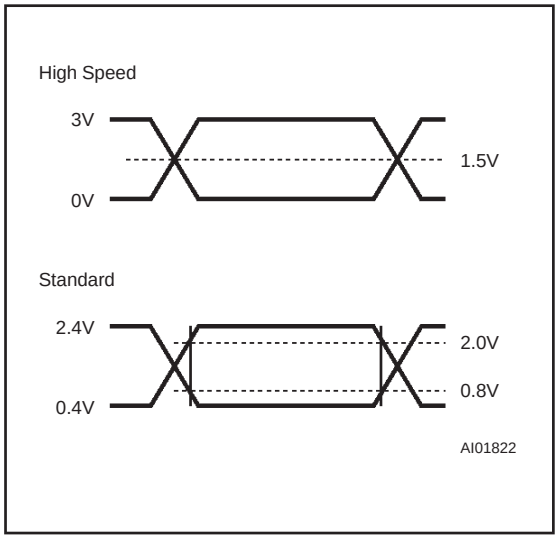


Figure 4. AC Testing Load Circuit

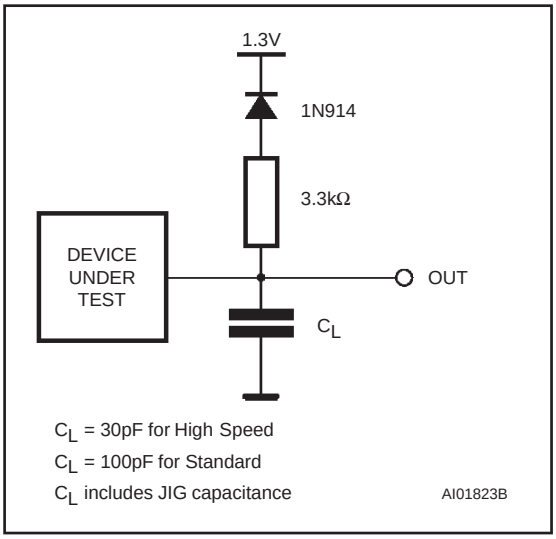


Table 6. Capacitance (1) (T_A = 25 °C, f = 1 MHz)

Symbol	Parameter	Test Condition	Min	Max	Unit
C_{IN}	Input Capacitance	V_{IN} = 0V		6	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0V		12	pF

Note: 1. Sampled only, not 100% tested.

Table 7. Read Mode DC Characteristics (1)
(T_A = 0 to 70 °C or –40 to 85 °C; V_{CC} = 5V ± 10%; V_{PP} = V_{CC})

Symbol	Parameter	Test Condition	Min	Max	Unit
I_{LI}	Input Leakage Current	$0V \le V_{IN} \le V_{CC}$		±10	µA
I_{LO}	Output Leakage Current	$0V \le V_{OUT} \le V_{CC}$		±10	µA
I_{CC}	Supply Current	$\overline{E} = V_{IL}$, $\overline{G} = V_{IL}$, I_{OUT} = 0mA, f = 5MHz		30	mA
I_{CC1}	Supply Current (Standby) TTL	$\overline{E} = V_{IH}$		1	mA
I_{CC2}	Supply Current (Standby) CMOS	$\overline{E} > V_{CC} - 0.2V$		100	µA
I_{PP}	Program Current	$V_{PP} = V_{CC}$		10	µA
V_{IL}	Input Low Voltage		–0.3	0.8	V
V_{IH} (2)	Input High Voltage		2	V_{CC} + 1	V
V_{OL}	Output Low Voltage	I_{OL} = 2.1mA		0.4	V
V_{OH}	Output High Voltage TTL	I_{OH} = –400µA	2.4		V
	Output High Voltage CMOS	I_{OH} = –100µA	V_{CC} – 0.7V		V

Notes: 1. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP}.
2. Maximum DC voltage on Output is V_{CC} +0.5V.

Table 8A. Read Mode AC Characteristics (1)
(T_A = 0 to 70 °C or –40 to 85 °C; V_{CC} = 5V ± 10%; V_{PP} = V_{CC})

Symbol	Alt	Parameter	Test Condition	M27C405						Unit
				-70 (3)		-80		-90		
				Min	Max	Min	Max	Min	Max	
t_{AVQV}	t_{ACC}	Address Valid to Output Valid	$\overline{E} = V_{IL}$, $\overline{G} = V_{IL}$		70		80		90	ns
t_{ELQV}	t_{CE}	Chip Enable Low to Output Valid	$\overline{G} = V_{IL}$		70		80		90	ns
t_{GLQV}	t_{OE}	Output Enable Low to Output Valid	$\overline{E} = V_{IL}$		35		40		40	ns
t_{EHQZ} (2)	t_{DF}	Chip Enable High to Output Hi-Z	$\overline{G} = V_{IL}$	0	30	0	30	0	30	ns
t_{GHQZ} (2)	t_{DF}	Output Enable High to Output Hi-Z	$\overline{E} = V_{IL}$	0	30	0	30	0	30	ns
t_{AXQX}	t_{OH}	Address Transition to Output Transition	$\overline{E} = V_{IL}$, $\overline{G} = V_{IL}$	0		0		0		ns

Notes: 1. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP}.
2. Sampled only, not 100% tested.
3. In case of 70ns speed see High Speed AC Measurement conditions.

Table 8B. Read Mode AC Characteristics (1)
(T_A = 0 to 70 °C or –40 to 85 °C; V_{CC} = 5V ± 10%; V_{PP} = V_{CC})

Symbol	Alt	Parameter	Test Condition	M27C405						Unit
				-100		-120		-150		
				Min	Max	Min	Max	Min	Max	
t_{AVQV}	t_{ACC}	Address Valid to Output Valid	$\overline{E}$ = V_{IL}, $\overline{G}$ = V_{IL}		100		120		150	ns
t_{ELQV}	t_{CE}	Chip Enable Low to Output Valid	$\overline{G}$ = V_{IL}		100		120		150	ns
t_{GLQV}	t_{OE}	Output Enable Low to Output Valid	$\overline{E}$ = V_{IL}		50		60		60	ns
t_{EHQZ} (2)	t_{DF}	Chip Enable High to Output Hi-Z	$\overline{G}$ = V_{IL}	0	30	0	40	0	50	ns
t_{GHQZ} (2)	t_{DF}	Output Enable High to Output Hi-Z	$\overline{E}$ = V_{IL}	0	30	0	40	0	50	ns
t_{AXQX}	t_{OH}	Address Transition to Output Transition	$\overline{E}$ = V_{IL}, $\overline{G}$ = V_{IL}	0		0		0		ns

Notes: 1. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP}.
2. Sampled only, not 100% tested.

Figure 5. Read Mode AC Waveforms

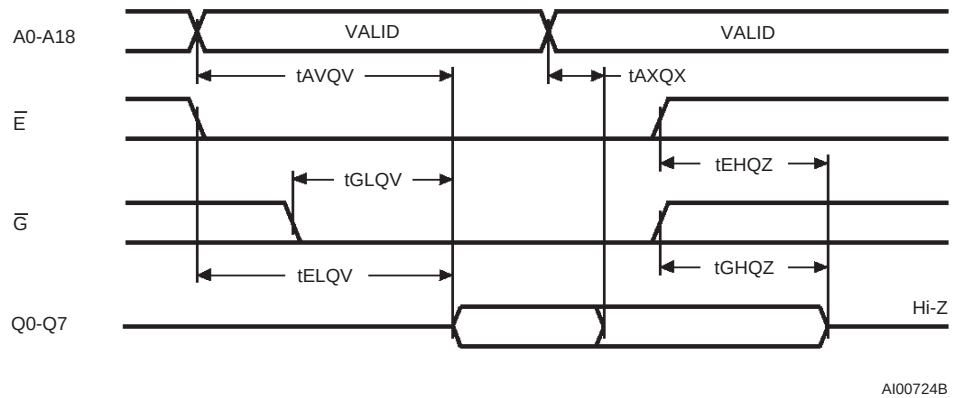


Table 9. Programming Mode DC Characteristics (1)
(T_A = 25 °C; V_{CC} = 6.25V ± 0.25V; V_{PP} = 12.75V ± 0.25V)

Symbol	Parameter	Test Condition	Min	Max	Unit
I_{LI}	Input Leakage Current	$0 \le V_{IN} \le V_{CC}$		±10	µA
I_{CC}	Supply Current			50	mA
I_{PP}	Program Current	$\overline{E} = V_{IL}$		50	mA
V_{IL}	Input Low Voltage		–0.3	0.8	V
V_{IH}	Input High Voltage		2	V_{CC} + 0.5	V
V_{OL}	Output Low Voltage	I_{OL} = 2.1mA		0.4	V
V_{OH}	Output High Voltage TTL	I_{OH} = –400µA	2.4		V
V_{ID}	A9 Voltage		11.5	12.5	V

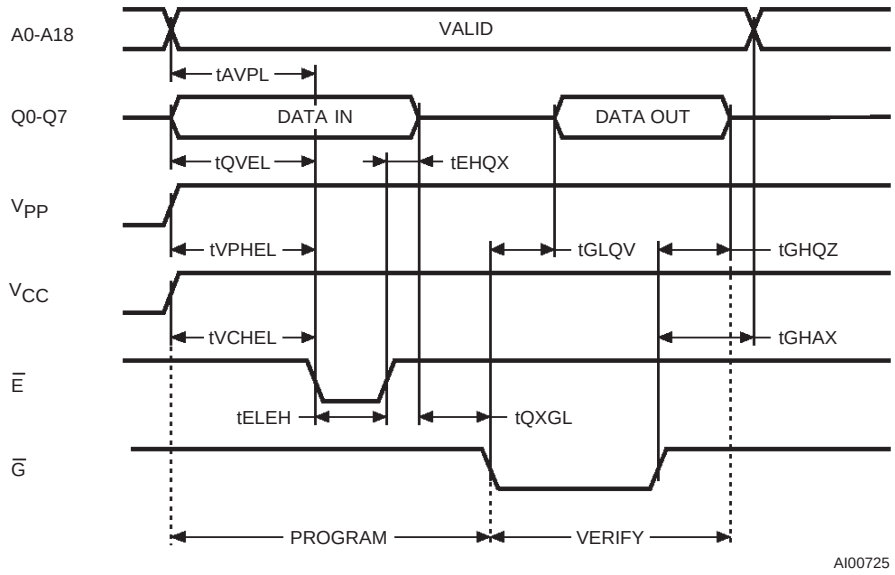
Note: 1. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP}.

Table 10. Programming Mode AC Characteristics (1)
(T_A = 25 °C; V_{CC} = 6.25V ± 0.25V; V_{PP} = 12.75V ± 0.25V)

Symbol	Alt	Parameter	Test Condition	Min	Max	Unit
t_{AVEL}	t_{AS}	Address Valid to Chip Enable Low		2		µs
t_{QVEL}	t_{DS}	Input Valid to Chip Enable Low		2		µs
t_{VPHEL}	t_{VPS}	V_{PP} High to Chip Enable Low		2		µs
t_{VCHEL}	t_{VCS}	V_{CC} High to Chip Enable Low		2		µs
t_{ELEH}	t_{PW}	Chip Enable Program Pulse Width		95	105	µs
t_{EHQX}	t_{DH}	Chip Enable High to Input Transition		2		µs
t_{QXGL}	t_{OES}	Input Transition to Output Enable Low		2		µs
t_{GLQV}	t_{OE}	Output Enable Low to Output Valid			100	ns
t_{GHQZ}	t_{DFP}	Output Enable High to Output Hi-Z		0	130	ns
t_{GHAX}	t_{AH}	Output Enable High to Address Transition		0		ns

Notes: 1. V_{CC} must be applied simultaneously with or before V_{PP} and removed simultaneously or after V_{PP}.
2. Sampled only, not 100% tested.

Figure 6. Programming and Verify Modes AC Waveforms



System Considerations

The power switching characteristics of Advanced CMOS OTP EPROMs require careful decoupling of the devices. The supply current, I_{CC}, has three segments that are of interest to the system designer : the standby current level, the active current level, and transient current peaks that are produced by the falling and rising edges of $\overline{E}$. The magnitude of the transient current peaks is dependent on the capacitive and inductive loading of the device at the output.

The associated transient voltage peaks can be suppressed by complying with the two line output control and by properly selected decoupling capacitors. It is recommended that a 0.1µF ceramic capacitor be used on every device between V_{CC} and V_{SS}. This should be a high frequency capacitor of low inherent inductance and should be placed as close to the device as possible. In addition, a 4.7µF bulk electrolytic capacitor should be used between V_{CC} and V_{SS} for every eight devices. The bulk capacitor should be located near the power supply connection point.The purpose of the bulk capacitor is to overcome the voltage drop caused by the inductive effects of PCB traces.

Programming

When delivered, all bits of the M27C405 are in the '1' state. Data is introduced by selectively programming '0's into the desired bit locations. Although only '0's will be programmed, both '1's and '0's can be present in the data word. The M27C405 is in the programming mode when V_{PP} input is at 12.75V, $\overline{G}$ is at V_{IH} and $\overline{E}$ is pulsed to V_{IL}. The data to be programmed is applied to 8 bits in parallel to the data output pins. The levels required for the address and data inputs are TTL. V_{CC} is specified to be 6.25V ± 0.25V.

Figure 7. Programming Flowchart

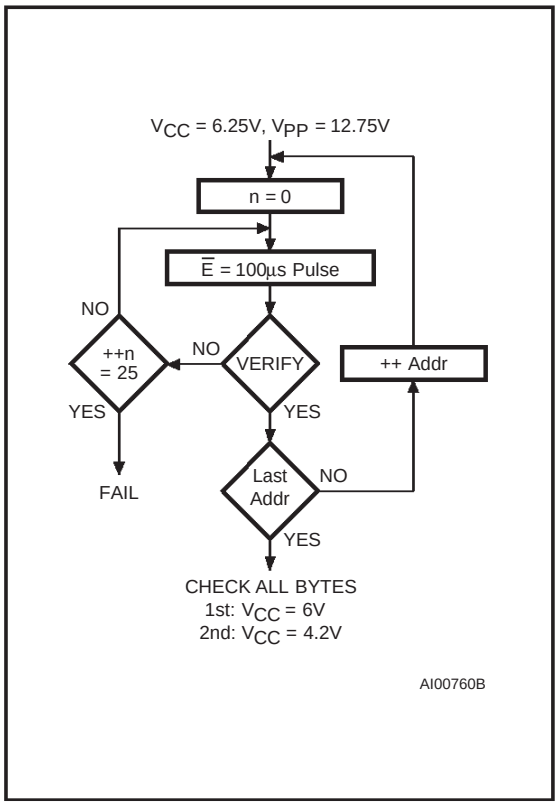
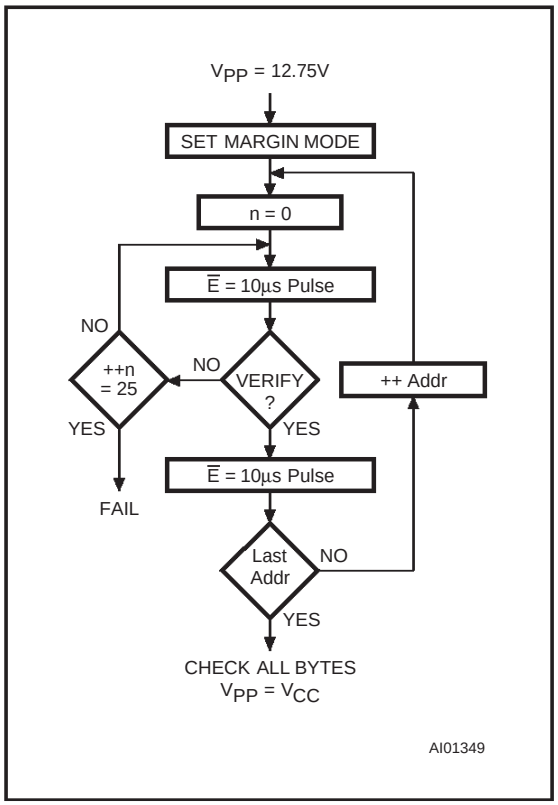


Figure 8. On-Board Programming Flowchart



PRESTO II Programming Algorithm

PRESTO II Programming Algorithm allows the whole array to be programmed with a guaranteed margin, in a typical time of 52.5 seconds. Programming with PRESTO II consists of applying a sequence of 100µs program pulses to each byte until a correct verify occurs (see Figure 7). During programming and verify operation, a MARGIN MODE circuit is automatically activated in order to guarantee that each cell is programmed with enough margin. No overprogram pulse is applied since the verify in MARGIN MODE provides the necessary margin to each programmed cell.

Program Inhibit

Programming of multiple M27C405s in parallel with different data is also easily accomplished. Except for $\overline{E}$, all like inputs including $\overline{G}$ of the parallel M27C405 may be common. A TTL low level pulse applied to a M27C405's $\overline{E}$ input, with V_{PP} at 12.75V, will program that M27C405. A high level $\overline{E}$ input inhibits the other M27C405s from being programmed.

Program Verify

A verify (read) should be performed on the programmed bits to determine that they were correctly programmed. The verify is accomplished with $\overline{G}$ at V_{IL} , $\overline{E}$ at V_{IH}, V_{PP} at 12.75V and V_{CC} at 6.25V.

On-Board Programming

Programming the M27C405 may be performed directly in the application circuit, however this requires modification to the PRESTO II Algorithm (see Figure 8). For in-circuit programming V_{CC} is determined by the user and normally is compatible with other components using the same supply voltage. It is recommended that the maximum value of V_{CC} which remains compatible with the circuit is used.

Typically V_{CC}=5.5V for programming systems using V_{CC}=5V is recommended. The value of V_{CC} does not affect the programming, it gives a higher test capability in VERIFY mode.

V_{PP} must be kept at 12.75 volts to maintain and enable the programming.

Warning: compatibility with FLASH Memory

Compatibility issues may arise when replacing the compatible Single Supply 4 Megabit FLASH Memory (the M29F040) by the M27C405.

The V_{PP} pin of the M27C405 corresponds to the "W" pin of the M29F040. The M27C405 V_{PP} pin can withstand voltages up to 12.75V, while the "W" pin of the M29F040 is a normal control signal input and may be damaged if a high voltage is applied; special precautions must be taken when programming in-circuit.

However if an already programmed M27C405 is used, this can be directly put in place of the FLASH Memory as the V_{PP} input, when not in programming mode, is set to V_{CC} or V_{SS}.

Changes to PRESTO II. The duration of the programming pulse is reduced to 20µs, making the programming time of the M27C405 comparable with the counterpart FLASH Memory.

Electronic Signature

The Electronic Signature (ES) mode allows the reading out of a binary code from an OTP EPROM that will identify its manufacturer and type. this mode is intended for use by programming equipment to automatically match the device to be programmed with its corresponding programming algorithm. This mode is functional in the 25°C ± 5°C ambient temperature range that is required when programming the M27C405. To activate the ES mode, the programming equipment must force 11.5V to 12.5V on address line A9 of the M27C405 with $V_{PP}=V_{CC}=5V$. Two identifier bytes may then be sequenced from the device outputs by toggling address line A0 from V_{IL} to V_{IH}. All other address lines must be held at V_{IL} during Electronic Signature mode. Byte 0 ($A0=V_{IL}$) represents the manufacturer code and byte 1 ($A0=V_{IH}$) the device identifier code. For the STMicroelectronics M27C405, these two identifier bytes are given in Table 4 and can be read-out on outputs Q0 to Q7.

ORDERING INFORMATION SCHEME

Example: M27C405 -80 K 1 TR

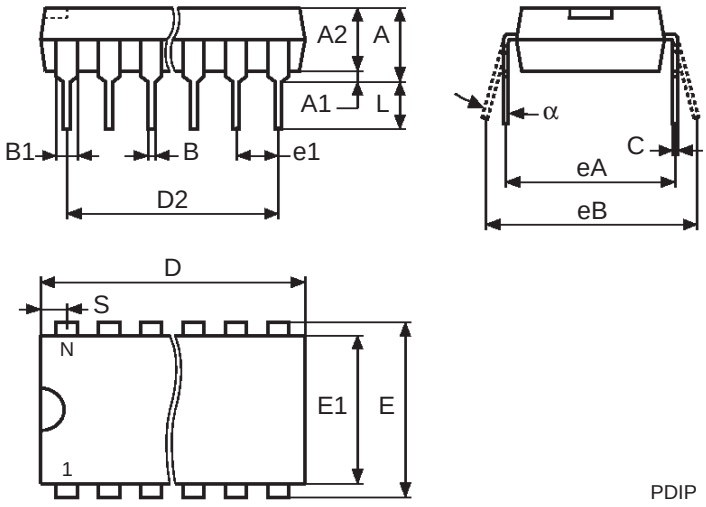
Speed		Package		Temperature Range		Option	
-70 (1)	70 ns	B	PDIP32	1	0 to 70 °C	TR	Tape & Reel Packing
-80	80 ns	K	PLCC32	6	–40 to 85 °C		
-90	90 ns	N	TSOP32 8 x 20mm				
-100	100 ns						
-120	120 ns						
-150	150 ns						

Note: 1. High Speed, see AC Characteristics section for further information.

For a list of available options (Speed, Package, etc...) or for further information on any aspect of this device, please contact the STMicroelectronics Sales Office nearest to you.

PDIP32 - 32 pin Plastic DIP, 600 mils width

Symb	mm			inches		
	Typ	Min	Max	Typ	Min	Max
A		–	5.08		–	0.200
A1		0.38	–		0.015	–
A2		3.56	4.06		0.140	0.160
B		0.38	0.51		0.015	0.020
B1	1.52	–	–	0.060	–	–
C		0.20	0.30		0.008	0.012
D		41.78	42.04		1.645	1.655
D2	38.10	–	–	1.500	–	–
E	15.24	–	–	0.600	–	–
E1		13.59	13.84		0.535	0.545
e1	2.54	–	–	0.100	–	–
eA	15.24	–		0.600	–	–
eB		15.24	17.–78		0.600	0.700
L		3.18	3.43		0.125	0.135
S		1.78	2.03		0.070	0.080
α		0°	10°		0°	10°
N	32			32		

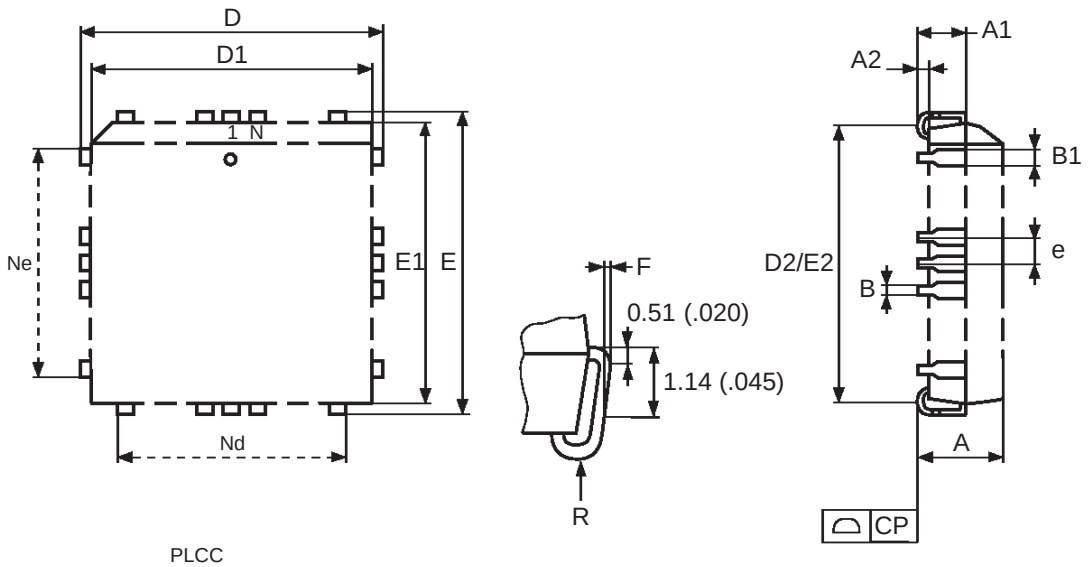


PDIP

Drawing is not to scale.

PLCC32 - 32 lead Plastic Leaded Chip Carrier, rectangular

Symb	mm			inches		
	Typ	Min	Max	Typ	Min	Max
A		2.54	3.56		0.100	0.140
A1		1.52	2.41		0.060	0.095
A2		–	0.38		–	0.015
B		0.33	0.53		0.013	0.021
B1		0.66	0.81		0.026	0.032
D		12.32	12.57		0.485	0.495
D1		11.35	11.56		0.447	0.455
D2		9.91	10.92		0.390	0.430
E		14.86	15.11		0.585	0.595
E1		13.89	14.10		0.547	0.555
E2		12.45	13.46		0.490	0.530
e	1.27	–	–	0.050	–	–
F		0.00	0.25		0.000	0.010
R	0.89	–	–	0.035	–	–
N	32			32		
Nd	7			7		
Ne	9			9		
CP			0.10			0.004

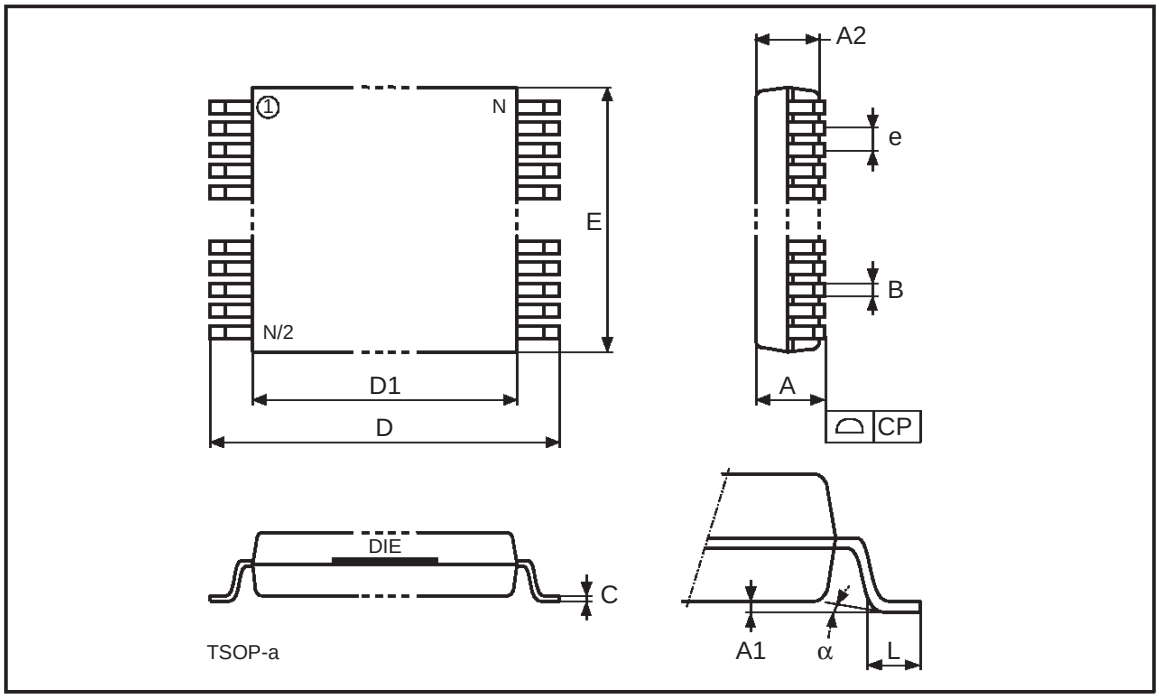


PLCC

Drawing is not to scale.

TSOP32 - 32 lead Plastic Thin Small Outline, 8 x 20mm

Symb	mm			inches		
	Typ	Min	Max	Typ	Min	Max
A			1.20			0.047
A1		0.05	0.15		0.002	0.007
A2		0.95	1.05		0.037	0.041
B		0.15	0.27		0.006	0.011
C		0.10	0.21		0.004	0.008
D		19.80	20.20		0.780	0.795
D1		18.30	18.50		0.720	0.728
E		7.90	8.10		0.311	0.319
e	0.50	-	-	0.020	-	-
L		0.50	0.70		0.020	0.028
α		0°	5°		0°	5°
N		32			32	
CP			0.10			0.004



TSOP-a

Drawing is not to scale.